



产品数据手册 Product Datasheet 版本 Ver 22.12

TG2000SW45ZC-P200

压接型 IGBT 模块 Press-pack IGBT Module

关键参数

Key Parameters

V_{CES}		4500	V
$V_{CE(sat)}$	Typ.	2.30	V
I_C	Max.	2000	A
$I_{C(RM)}$	Max.	4000	A

典型应用

Typical Applications

- | | |
|----------|------------------------------|
| ● 柔直换流阀 | MMC-HVDC Valve |
| ● 直流断路器 | DC Breaker |
| ● 海上风电 | Off-shore Wind Power |
| ● 大型工业传动 | Large-scale Industrial Drive |

特点

Features

- | | |
|----------|---------------------------------|
| ● 双面散热 | Double-side Cooling |
| ● 失效短路 | Short-circuit Failure Mode |
| ● 高热循环能力 | High Thermal Cycling Capability |
| ● 低杂散电感 | Low Stray Inductance |

电路结构

Circuit Configuration

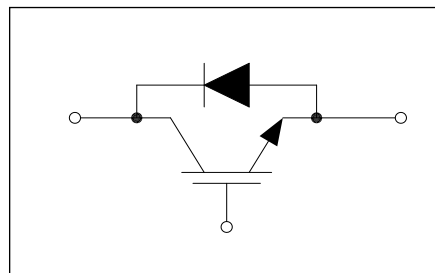


图 1. 电路结构

Fig. 1 Circuit configuration

模块外形

Module Appearance



图 2. 模块外形

Fig. 2 Module appearance

模块标签说明

Module Label Code Instruction

 18BC00670027	数据位置 Data position	数据内容 Content of data
	1—8	模块批次号 Module batch number
	9—12	模块序列号 Module serial number

最大额定值
Absolute Maximum Ratings

符号 Symbol	参数名称 Parameter	测试条件 Test Conditions	数值 Value	单位 Unit
V_{CES}	集电极-发射极电压 Collector-emitter voltage	$V_{GE} = 0V, T_C = 25\text{ }^{\circ}\text{C}$	4500	V
V_{GES}	栅极-发射极电压 Gate-emitter voltage	$T_C = 25\text{ }^{\circ}\text{C}$	± 20	V
I_C	集电极电流 Collector-emitter current	$T_C = 95\text{ }^{\circ}\text{C}$	2000	A
$I_{C(PK)}$	集电极峰值电流 Peak collector current	$t_P = 1\text{ms}$	4000	A
P_{max}	晶体管部分最大损耗 Max. transistor power dissipation	$T_{vj} = 125\text{ }^{\circ}\text{C}, T_C = 25\text{ }^{\circ}\text{C}$	22.2	kW
I_{FSM}	二极管浪涌电流 Diode Surge Current	$V_R = 0V, t_P = 10\text{ms}, T_{vj} = 125\text{ }^{\circ}\text{C}$	15	kA



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热和机械数据

Thermal & Mechanical Data

符号 Symbol	参数名称 Parameter	测试条件 Test Conditions	最小值 Min.	典型值 Typ.	最大值 Max.	单位 Unit
$R_{th(J-C)} IGBT$	IGBT 结壳热阻 Thermal resistance – IGBT	双面散热 Double-side cooling			4.3	K / kW
$R_{th(J-C)} Diode$	二极管结壳热阻 Thermal resistance – Diode	双面散热 Double-side cooling			8.6	K / kW
$R_{th(C-H)} IGBT$	接触热阻(IGBT) Thermal resistance – case to heatsink (IGBT)	压装力 75kN Clamping Force 75kN		0.8		K / kW
$R_{th(C-H)} Diode$	接触热阻(Diode) Thermal resistance – case to heatsink (Diode)	压装力 75kN Clamping Force 75kN		1.7		K / kW
T_{vj}	工作结温 Operating junction temperature	IGBT 部分 (IGBT)			125	°C
		二极管部分(Diode)			125	°C
T_{stg}	存储温度 Storage temperature range		-40		125	°C
M	压装力 Clamping Force		70		85	kN

Caution: This device is sensitive to electrostatic discharge. Users should follow ESD handling procedures.

注意：该器件对静电敏感，用户须采取 ESD 防护措施。

电特性值
Electrical Characteristics

除非特别声明, 否则 $T_C = 25\text{ }^{\circ}\text{C}$
 $T_C = 25\text{ }^{\circ}\text{C}$ unless otherwise stated

符号 Symbol	参数名称 Parameter	条件 Test Conditions	最小值 Min.	典型值 Typ.	最大值 Max.	单位 Unit
I_{CES}	集电极截止电流 Collector cut-off current	$V_{GE} = 0V, V_{CE} = V_{CES}$			1	mA
		$V_{GE} = 0V, V_{CE} = V_{CES}, T_C = 125\text{ }^{\circ}\text{C}$		30	100	mA
I_{GES}	栅极漏电流 Gate leakage current	$V_{GE} = \pm 20V, V_{CE} = 0V$			500	nA
$V_{GE(TH)}$	栅极-发射极阈值电压 Gate threshold voltage	$I_C = 200mA, V_{GE} = V_{CE}$	5.5	6.0	6.5	V
$V_{CE(sat)}$	集电极-发射极饱和电压 Collector-emitter saturation voltage	$V_{GE} = 15V, I_C = 2000A$		2.30	2.70	V
		$V_{GE} = 15V, I_C = 2000A, T_{vj} = 125\text{ }^{\circ}\text{C}$		2.95	3.35	V
I_F	二极管正向直流电流 Diode forward current	DC		2000		A
I_{FRM}	二极管正向重复峰值电流 Diode peak forward current	$t_p = 1ms$		4000		A
V_F	二极管正向电压 Diode forward voltage	$I_F = 2000A, V_{GE} = 0$		2.45	2.85	V
		$I_F = 2000A, V_{GE} = 0, T_{vj} = 125\text{ }^{\circ}\text{C}$		2.70	3.10	V
I_{SC}	短路电流 Short circuit current	$T_{vj} = 125\text{ }^{\circ}\text{C}, V_{CC} = 3400V,$ $V_{GE} \leq 15V, t_p \leq 10\mu s,$ $V_{CE(max)} = V_{CES} - L \times di/dt,$ IEC 60747-9		8300		A



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电特性值

Electrical Characteristics

除非特别声明, 否则 $T_C = 25\text{ }^{\circ}\text{C}$ $T_C = 25\text{ }^{\circ}\text{C}$ unless otherwise stated

符号 Symbol	参数名称 Parameter	条件 Test Conditions	最小值 Min.	典型值 Typ.	最大值 Max.	单位 Unit
C_{ies}	输入电容 Input capacitance	$V_{CE} = 25V, V_{GE} = 0V, f = 100kHz$		315		nF
Q_g	栅极电荷 Gate charge	$\pm 15V$		24		μC
C_{res}	反向传输电容 Reverse transfer capacitance	$V_{CE} = 25V, V_{GE} = 0V, f = 100kHz$		5.4		nF
C_{oes}	输出电容 Output capacitance	$V_{CE} = 25V, V_{GE} = 0V, f = 100kHz$		20		nF
L_M	模块电感 Module inductance			2		nH

电特性值
Electrical Characteristics

符号 Symbol	参数名称 Parameter	条件 Test Conditions		最小值 Min.	典型值 Typ.	最大值 Max.	单位 Unit
$t_{d(off)}$	关断延迟时间 Turn-off delay time	$I_C = 2000A,$ $V_{CE} = 2800V,$ $V_{GE} = \pm 15V,$ $R_{G(OFF)} = 8.2\Omega,$ $C_{GE} = 330nF,$ $L_S = 150nH$	$T_{vj} = 25\text{ }^{\circ}C$		6530		ns
			$T_{vj} = 125\text{ }^{\circ}C$		6770		
t_f	下降时间 Fall time		$T_{vj} = 25\text{ }^{\circ}C$		1600		ns
			$T_{vj} = 125\text{ }^{\circ}C$		2800		
E_{OFF}	关断损耗 Turn-off energy loss		$T_{vj} = 25\text{ }^{\circ}C$		9.0		J
			$T_{vj} = 125\text{ }^{\circ}C$		10.9		
$t_{d(on)}$	开通延迟时间 Turn-on delay time	$I_C = 2000A,$ $V_{CE} = 2800V,$ $V_{GE} = \pm 15V,$ $R_{G(ON)} = 1.8\Omega,$ $C_{GE} = 330nF,$ $L_S = 150nH,$ $di/dt = 3200A/us,$ ($T_{vj} = 125\text{ }^{\circ}C$)	$T_{vj} = 25\text{ }^{\circ}C$		730		ns
			$T_{vj} = 125\text{ }^{\circ}C$		720		
t_r	上升时间 Rise time		$T_{vj} = 25\text{ }^{\circ}C$		430		ns
			$T_{vj} = 125\text{ }^{\circ}C$		500		
E_{ON}	开通损耗 Turn-on energy loss		$T_{vj} = 25\text{ }^{\circ}C$		9.4		J
			$T_{vj} = 125\text{ }^{\circ}C$		12.7		
Q_{rr}	二极管反向恢复电荷 Diode reverse recovery charge	$I_F = 2000A,$ $V_{CE} = 2800V,$ - $di_F/dt = 3200A/us,$ ($T_{vj} = 125\text{ }^{\circ}C$)	$T_{vj} = 25\text{ }^{\circ}C$		1650		μC
			$T_{vj} = 125\text{ }^{\circ}C$		2920		
I_{rr}	二极管反向恢复电流 Diode reverse recovery current		$T_{vj} = 25\text{ }^{\circ}C$		1800		A
			$T_{vj} = 125\text{ }^{\circ}C$		1820		
E_{rec}	二极管反向恢复损耗 Diode reverse recovery energy		$T_{vj} = 25\text{ }^{\circ}C$		2.4		J
			$T_{vj} = 125\text{ }^{\circ}C$		4.3		

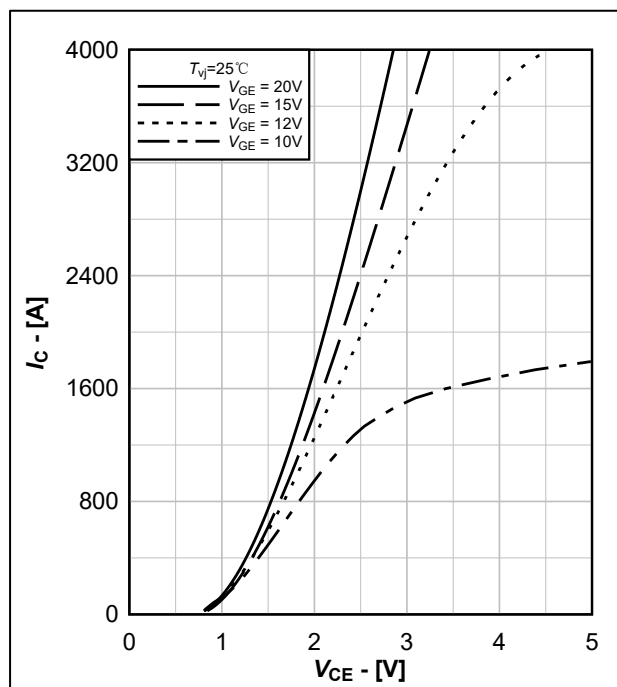
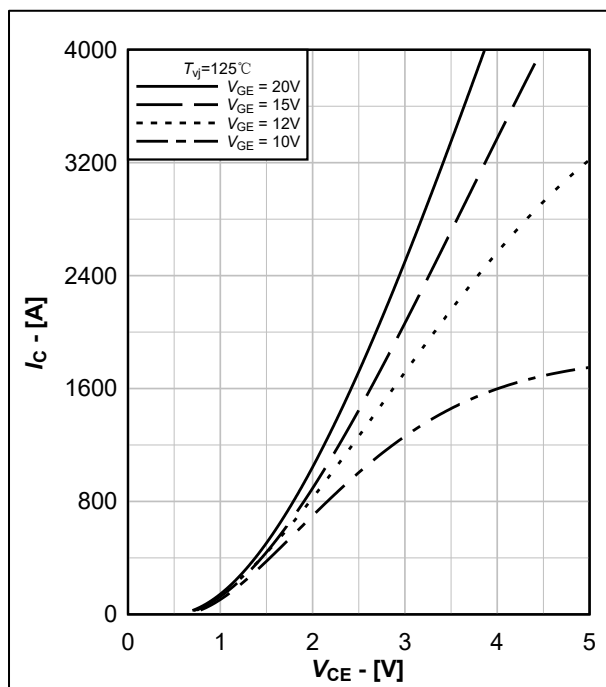
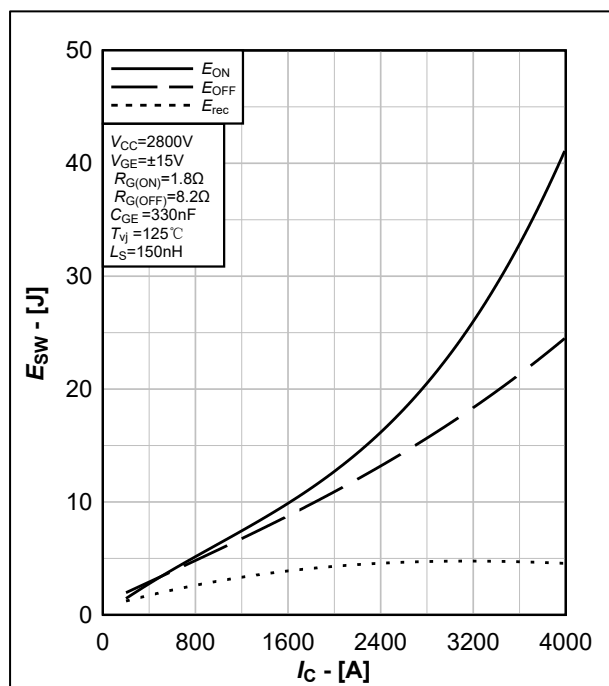
图 3. IGBT 输出特性典型曲线, $I_C = f(V_{CE})$ Fig.3 Typical IGBT output characteristics, $I_C = f(V_{CE})$ 图 4. IGBT 输出特性典型曲线, $I_C = f(V_{CE})$ Fig.4 Typical IGBT output characteristics, $I_C = f(V_{CE})$ 

图 5. IGBT 及 FRD 开关能耗典型曲线,

$$E_{ON} = f(I_C), E_{OFF} = f(I_C), E_{rec} = f(I_C)$$

Fig.5 Typical IGBT & FRD switching energy,

$$E_{ON} = f(I_C), E_{OFF} = f(I_C), E_{rec} = f(I_C)$$

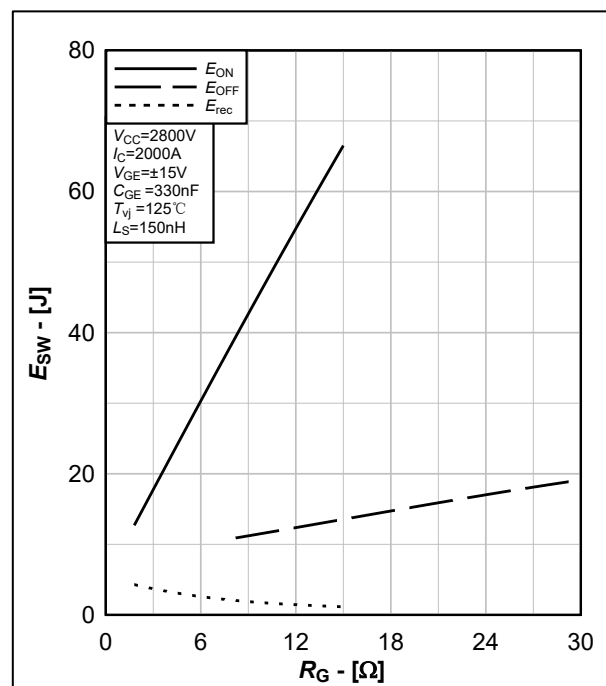


图 6. IGBT 及 FRD 开关能耗典型曲线,

$$E_{ON} = f(R_G), E_{OFF} = f(R_G), E_{rec} = f(R_G)$$

Fig.6 Typical IGBT & FRD switching energy,

$$E_{ON} = f(R_G), E_{OFF} = f(R_G), E_{rec} = f(R_G)$$

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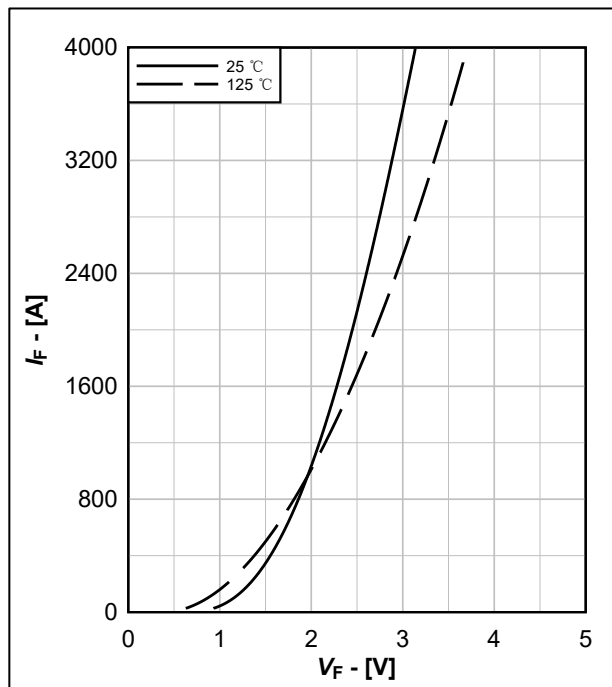

图 7. FRD 输出特性典型曲线, $I_F = f(V_F)$

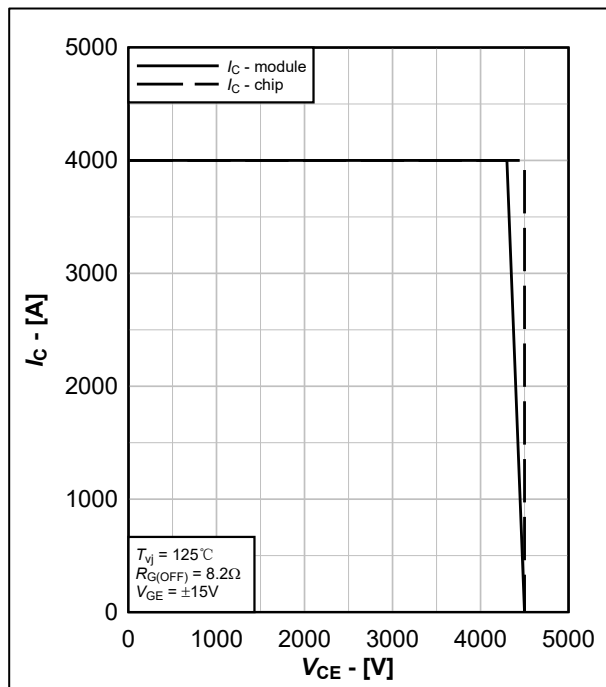
Fig.7 Typical FRD output characteristics, $I_F = f(V_F)$


图 8. IGBT 反偏安全工作区

Fig.8 Reverse bias safe operating area of IGBT

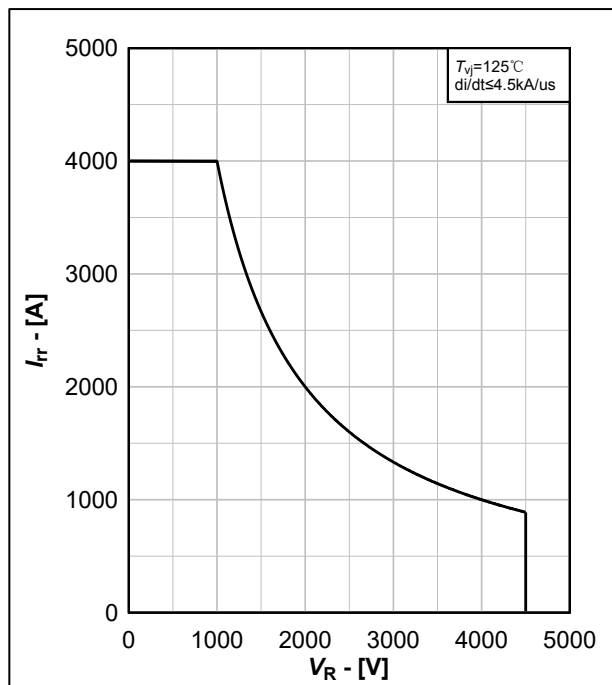


图 9. 二极管反偏安全工作区

Fig.9 Reverse bias safe operating area of Diode

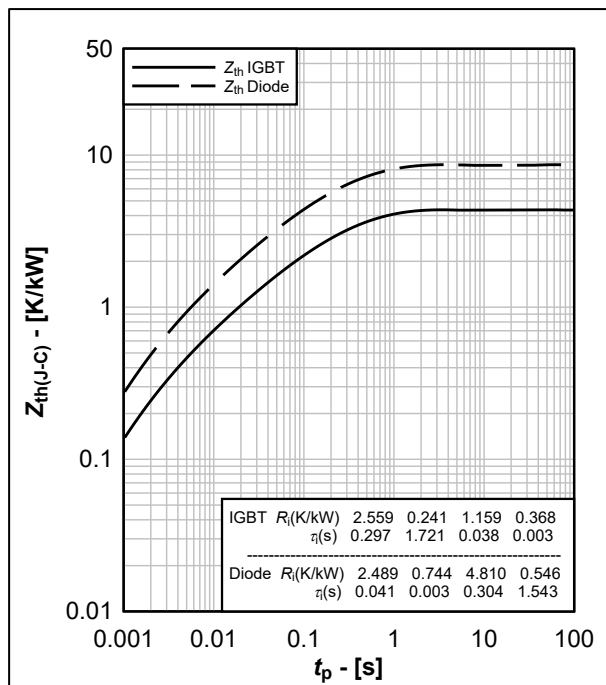
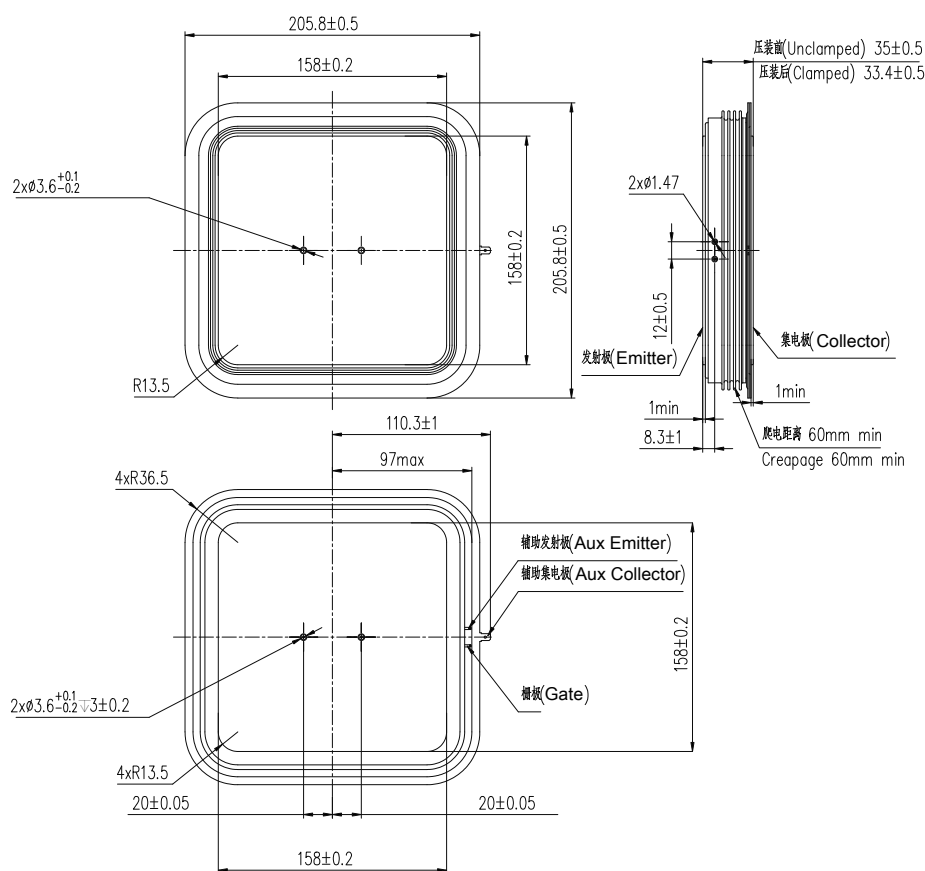

图 10. 瞬态热阻抗曲线, $Z_{th(j-c)} = f(t_p)$

Fig.10 Transient thermal impedance, $Z_{th(j-c)} = f(t_p)$



重量 Weight: 5000g

模块外观类型 Module outline code: ZC

图 11. 模块外观尺寸

Fig. 11 Module outlines

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